

The invention relates to the field of photonics, namely to the photon registration plants, in particular to the photosensitive cells of the photodetectors on base of semiconductors.

The photosensitive cell of the photodetector comprises a glass substrate (1), onto which there are applied a contact layer (2), a photosensitive semiconductor layer (3) of arsenous triselenide (As_2Se_3) doped with stannum (Sn) with a concentration within the limits of 3.0...5.0 at.%, and a second contact layer (4).

The result consists in that the photosensitive cell allows a more precise registration of photons, possesses increased photoelectric sensitivity and a high-capacity photoelectric memory.

Claims: 1

Fig.: 2

